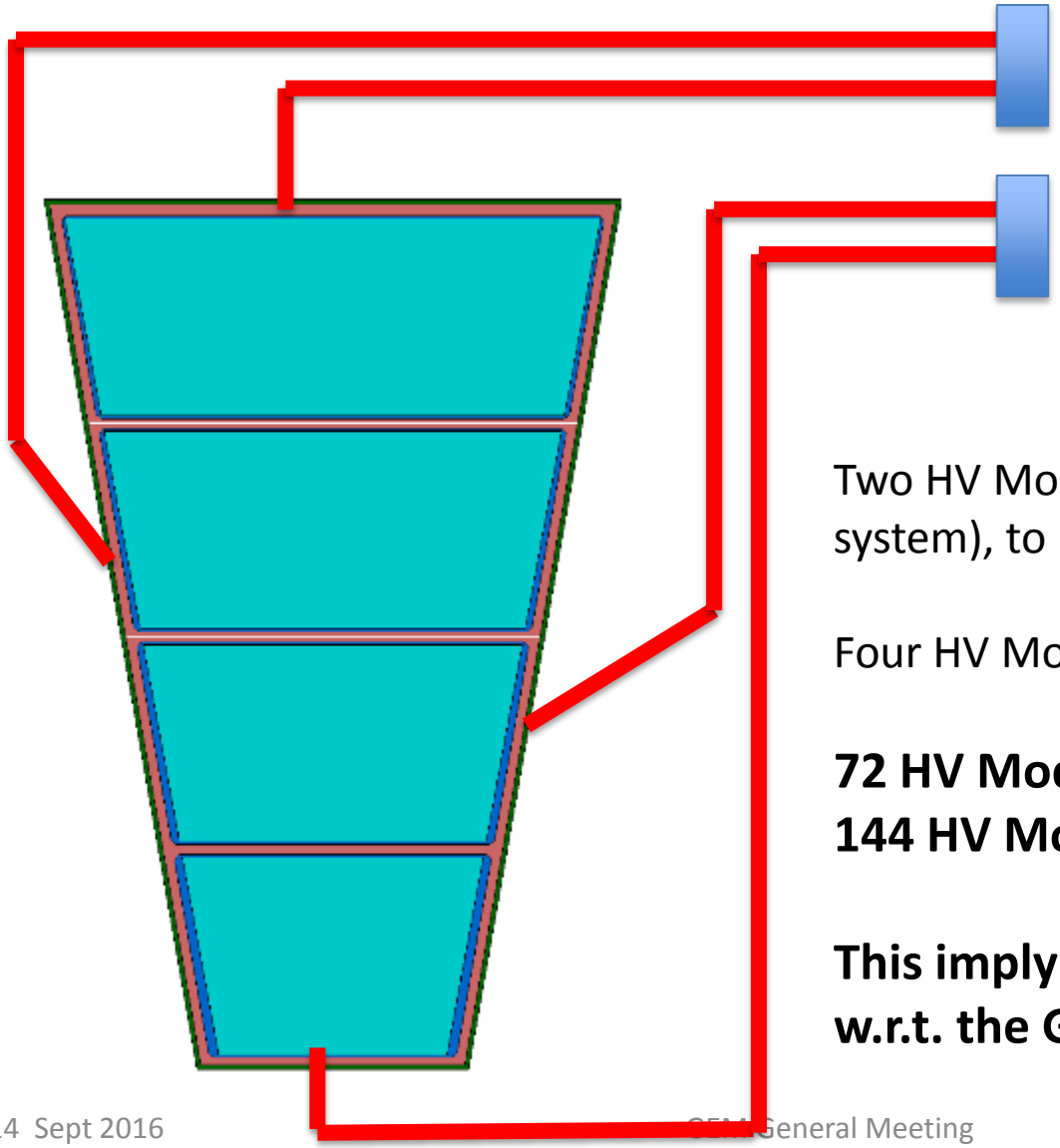
HV schema for GE2/1 : Option A
28 ch. per chamber (56 ch. Per super-chamber)



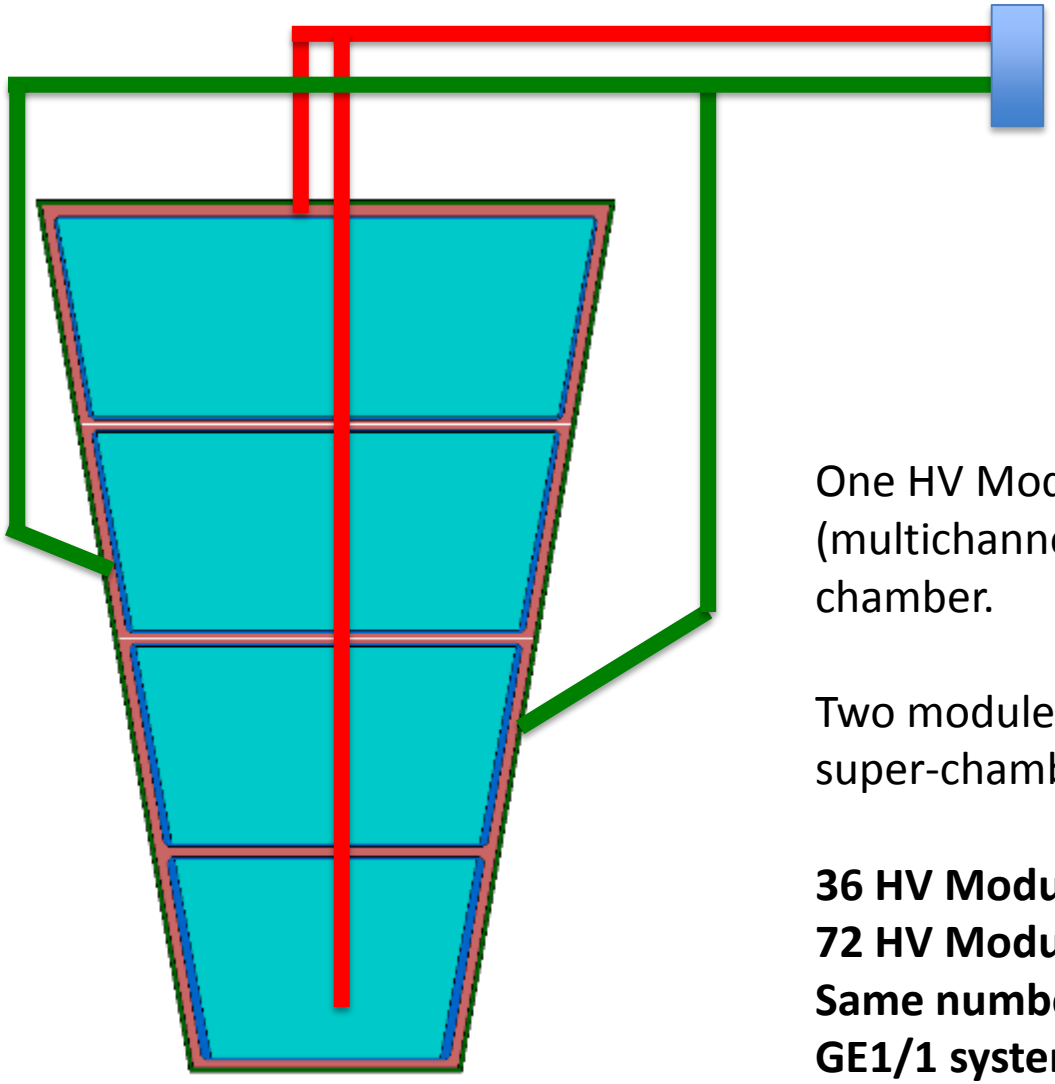
Two HV Module, GE1/1 model, (multichannel system), to power one GE2/1 chamber.

Four HV Module for a super chamber

72 HV Modules (x 7 channel) per EndCap
144 HV Modules in total

This imply double number of HV board w.r.t. the GE1/1 power system

HV schema for GE2/1 : Option A
14 ch. per chamber (24 ch. Per super-chamber)



One HV Module, GE1/1 model (multichannel system), to power one GE2/1 chamber.

Two modules will be necessary to power a super-chamber which will cover 20 Deg.

36 HV Modules (x 7 channel) per EndCap
72 HV Modules in total
Same number of HV board used in the GE1/1 system

- A single HV sector in short will absorb ~45 microA (450 V / 10 M ohm – protection resistance), the max number of HV sector which we can supply will be I_0max /45
- In GE1/1 we have 47/40 HV sectors in Long/Short foil
- In M4 of GE2/1 will have 50 HV (~ 42 M3, ~34 M2, ~26 M1)
- Powering M4+M1 and M2+M3 each HV channel will provide power up to 76 HV sectors, the relative fraction of acceptable “dead sectors” will be about ½ w.r.t. the GE1/1 fraction
- To reduce the current absorbed by the single sector may we can change the value of the protection resistance, to be investigated with Rui.